

Supporting information

Towards low-temperature processing of efficient γ -CsPbI₃ perovskite solar cells

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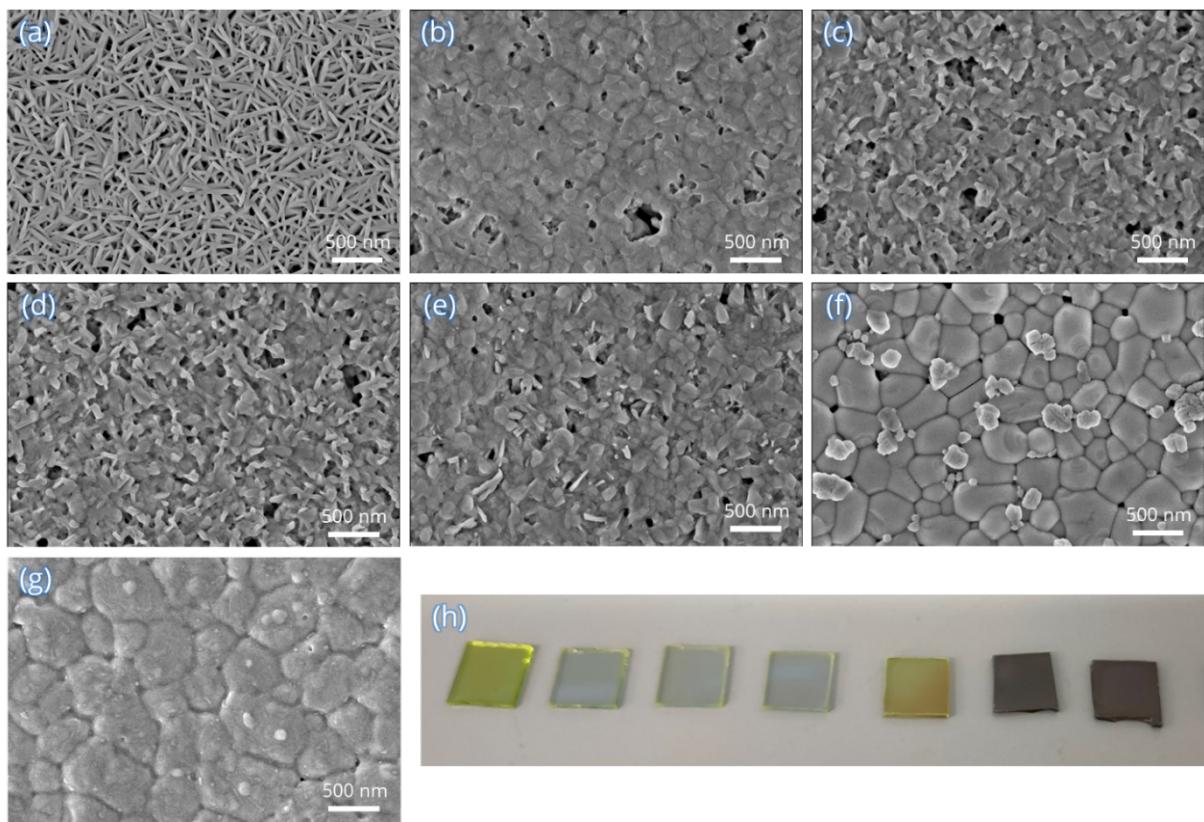


Fig. S1 Top-view SEM of perovskite with the aid of $\text{Pb}(\text{OAc})_2$ and EDAI_2 undergoing different thermal annealing temperatures: (a) as-deposited wet film, (b) preheat at $60\text{ }^\circ\text{C}$ for 1 min, (c) preheat at $60\text{ }^\circ\text{C}$ for 3 min, (d) preheat at $60\text{ }^\circ\text{C}$ for 5 min, (e) annealing at $180\text{ }^\circ\text{C}$ for 5 s, (f) annealing at $180\text{ }^\circ\text{C}$ for 30 s, (g) annealing at $180\text{ }^\circ\text{C}$ for 3 min. And corresponding the film images are shown in (h).

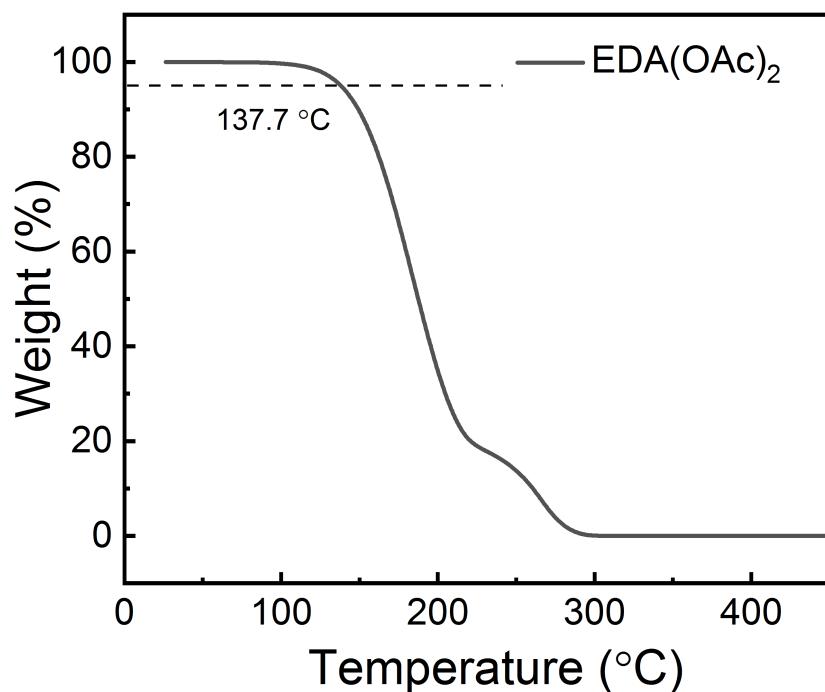


Fig. S2 TGA curves for $\text{EDA}(\text{OAc})_2$ in nitrogen atmosphere.

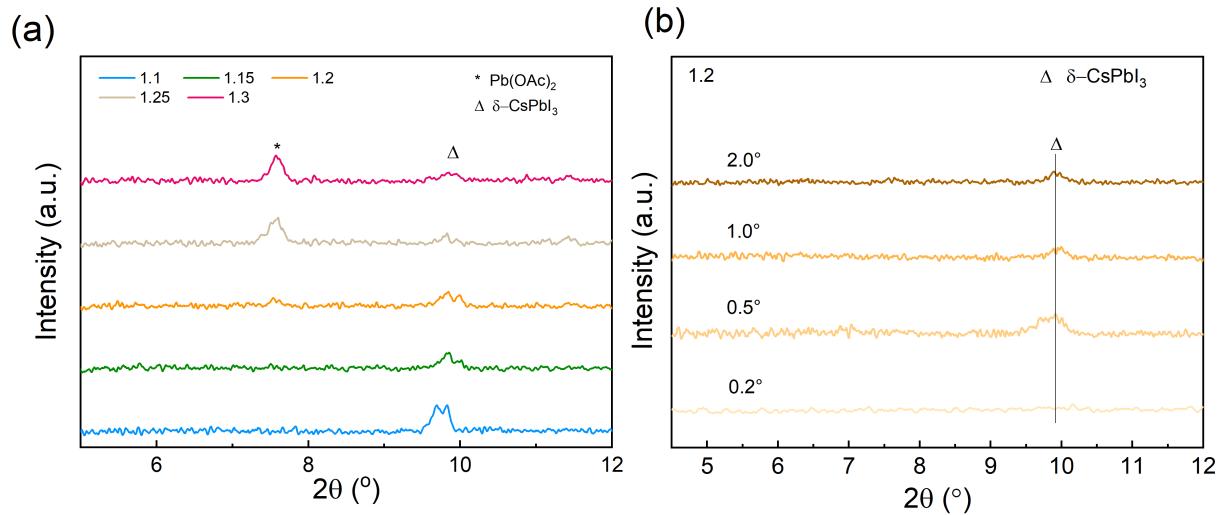


Fig. S3 (a) XRD patterns of CsPbI₃ with different Pb(OAc)₂ ratios at the low angle range, (b) Grazing incidence x-ray diffraction (GIXRD) patterns of 1.2 CsPbI₃ samples with different Ω values at low angles.

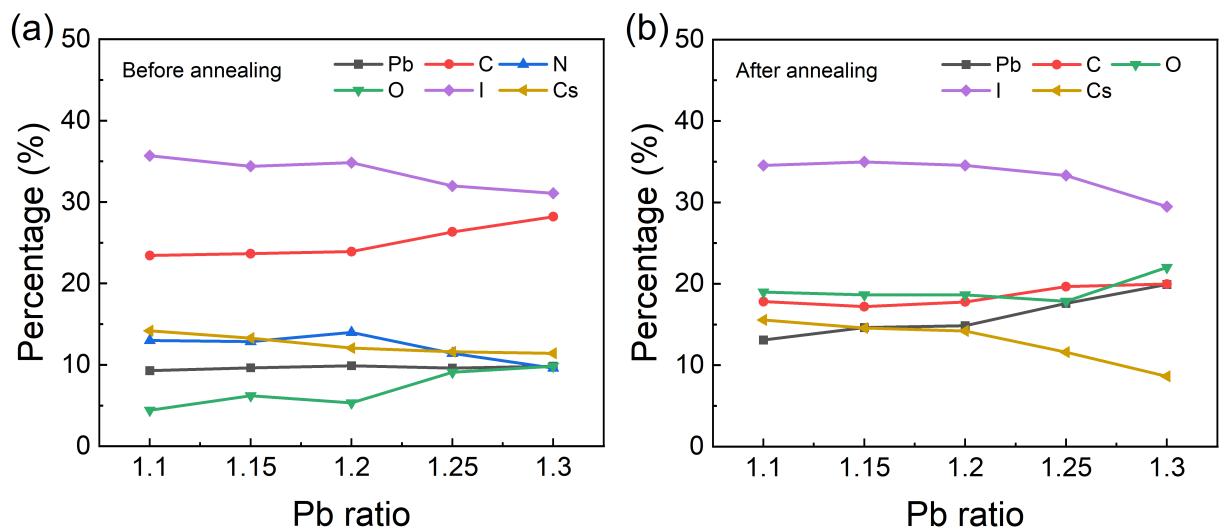


Fig. S4 Element concentration for different ratios of Pb(OAc)₂ (a) after preheating at 60 °C, but before annealing at 180 °C and (b) after annealing at 180 °C for 3 minutes.

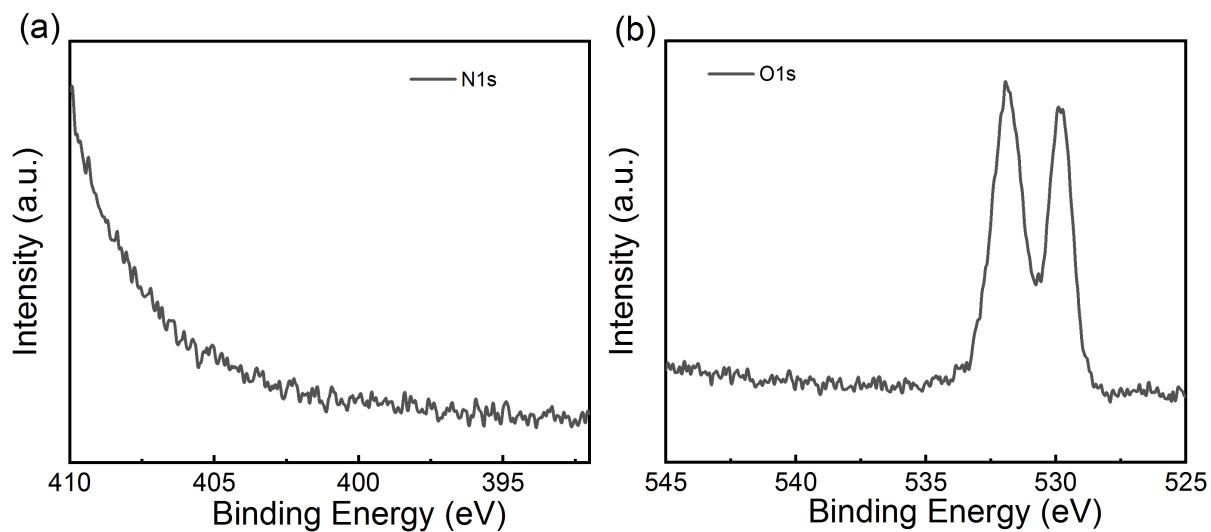
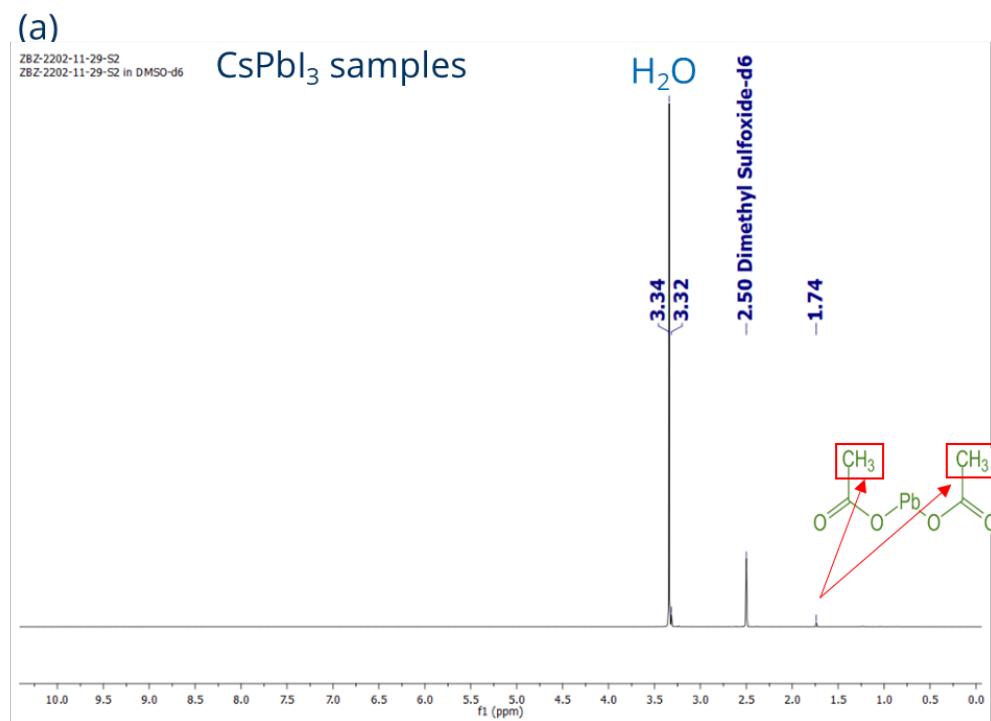


Fig. S5 (a) N1s and (b) O1s XPS spectra in 1.2 CsPbI₃ film after annealing.



(b)

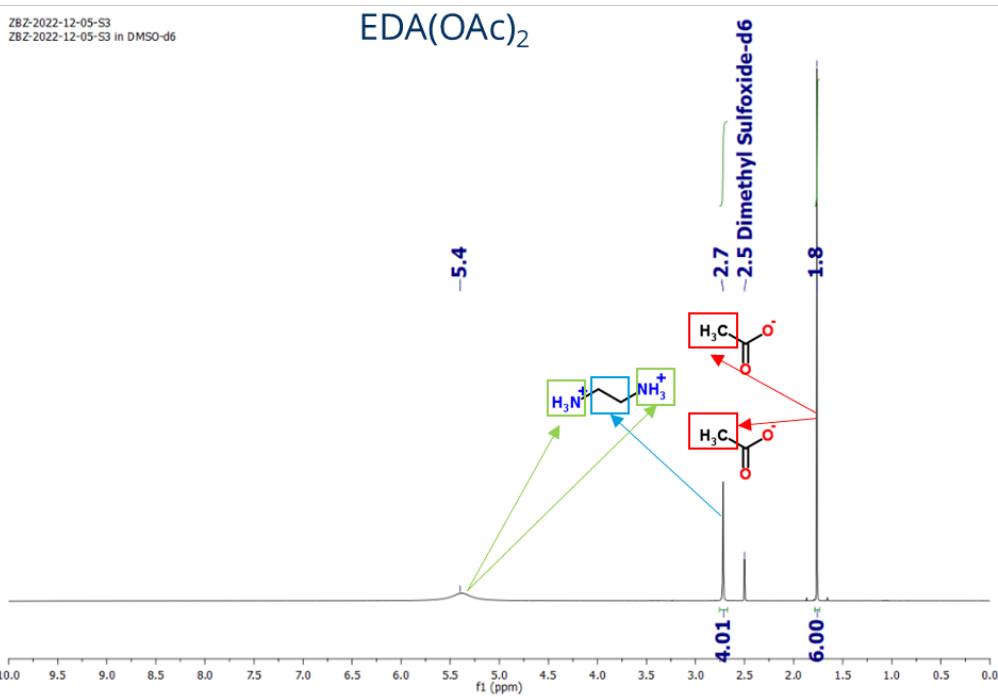
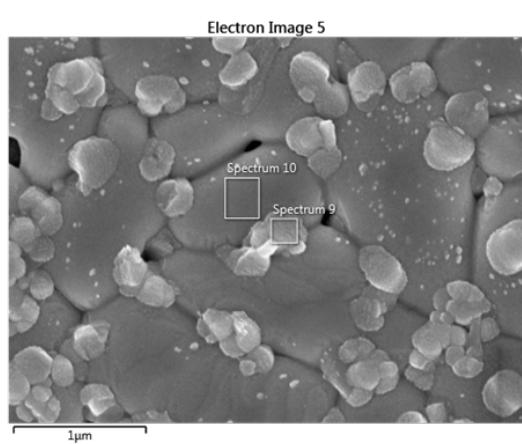
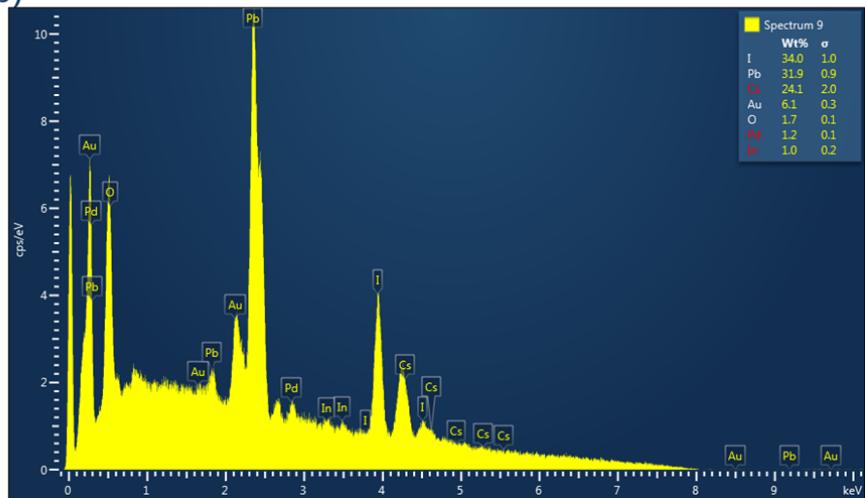


Fig. S6 H-NMR of final CsPbI₃ and intermediate EDA(OAc)₂ products in DMSO-D6 solvent.
For the CsPbI₃ samples, scratched powder from the film dissolves in the DMSO-D6 solvent.

(a)



(b)



(c)

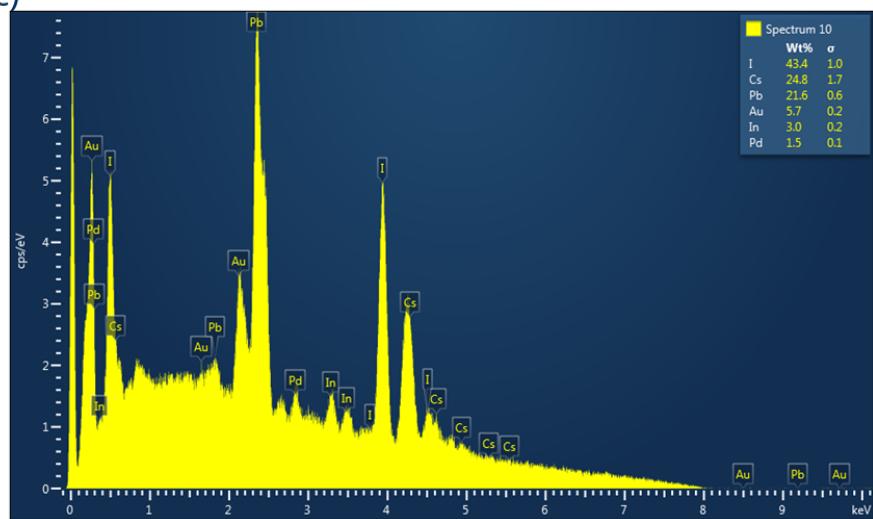


Fig. S7 (a) Top-view SEM images and (b), (c) corresponding EDX element composition spectra in 1.25 samples.

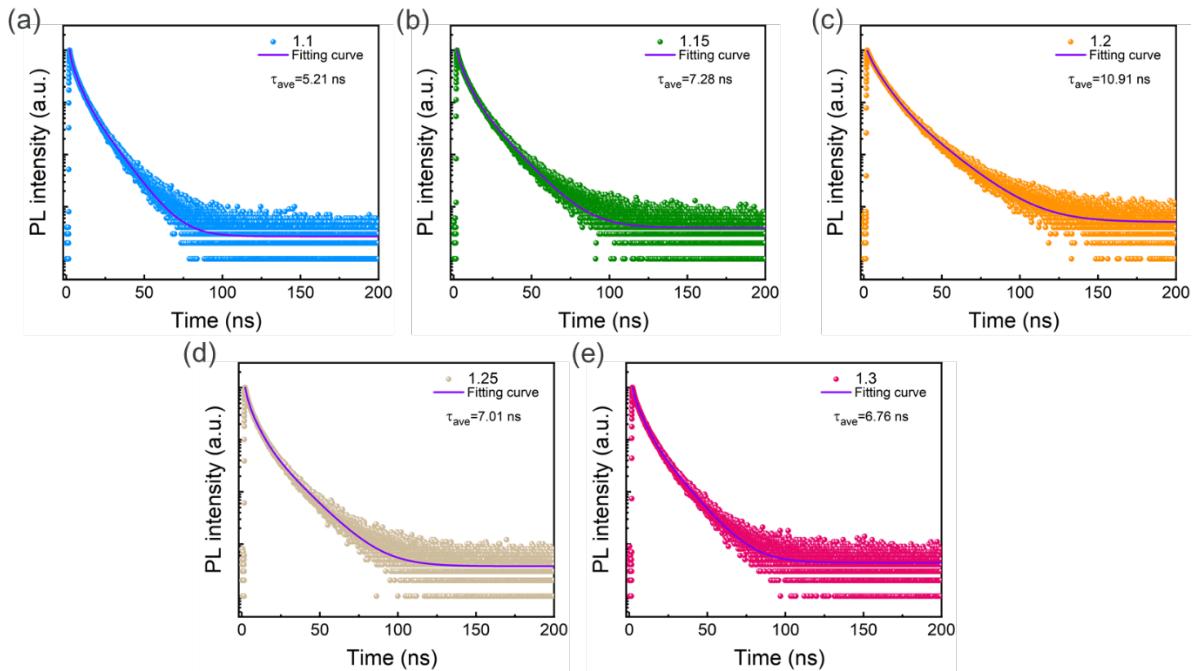


Fig. S8 TRPL fitting curves for different amount of $\text{Pb}(\text{OAc})_2$: (a) 1.1, (b) 1.15, (c) 1.2, (d) 1.25, (e) 1.3. The carrier lifetime was obtained by fitting TRPL curves using the following formula: $y = A_1 e^{-x_1/\tau_1} + A_2 e^{-x_2/\tau_2} + A_3 e^{-x_3/\tau_3} + B$. The average carrier lifetime was calculated by the equation: $\tau_{ave} = (\sum A_i \tau_i^2) / (\sum A_i \tau_i)$. The related parameters are summarized in the Table S2.

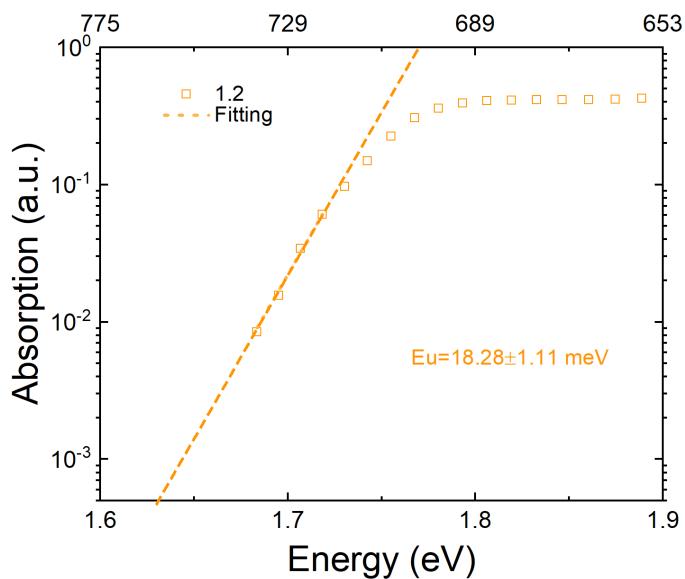


Fig. S9 Photothermal deflection spectroscopy (PDS) of 1.2 sample.

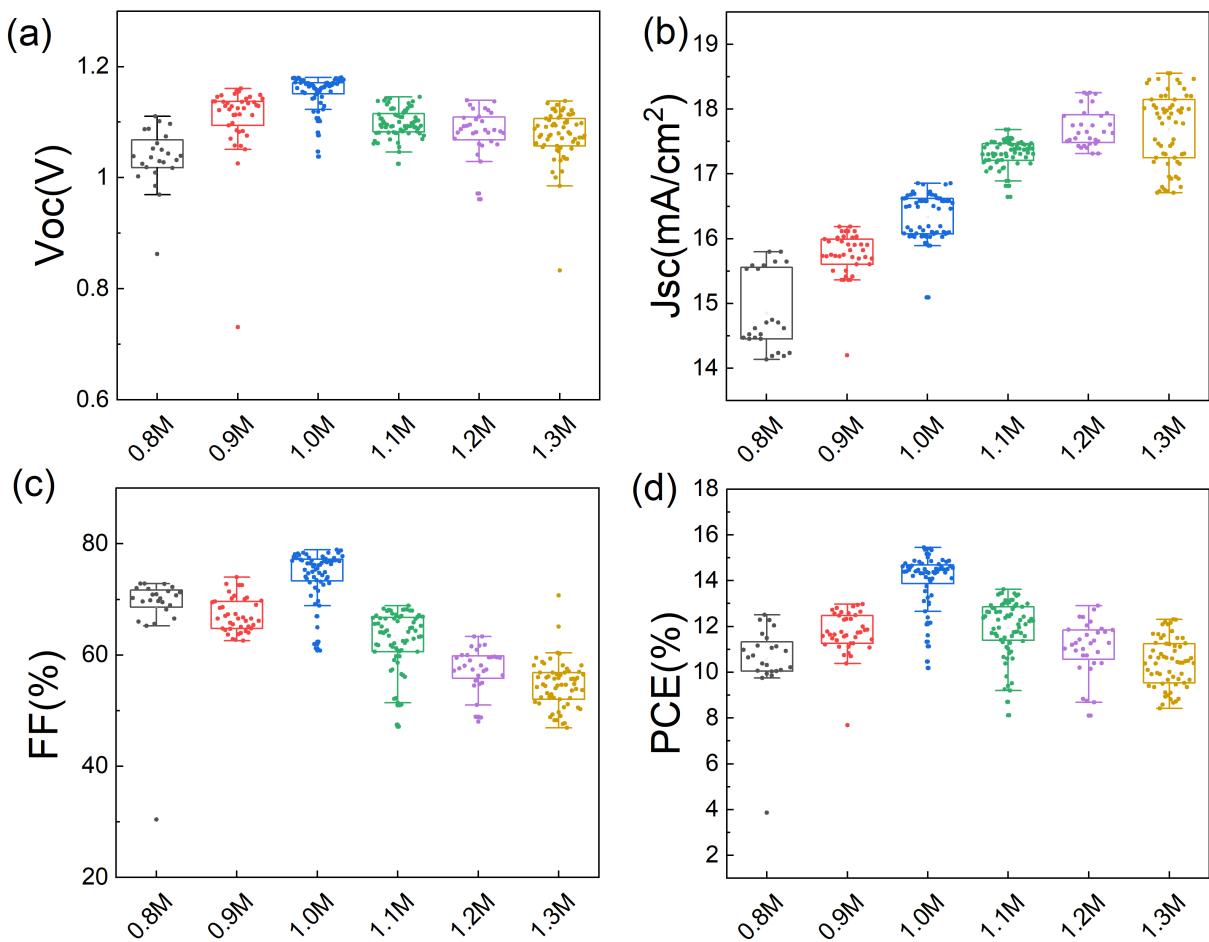


Fig. S10 Photovoltaic performance parameters: (a) V_{OC} , (b) J_{SC} , (c) FF and (d) PCE distribution of different perovskite precursor concentrations in 1.2 CsPbI₃ devices. A total of 290 devices were measured.

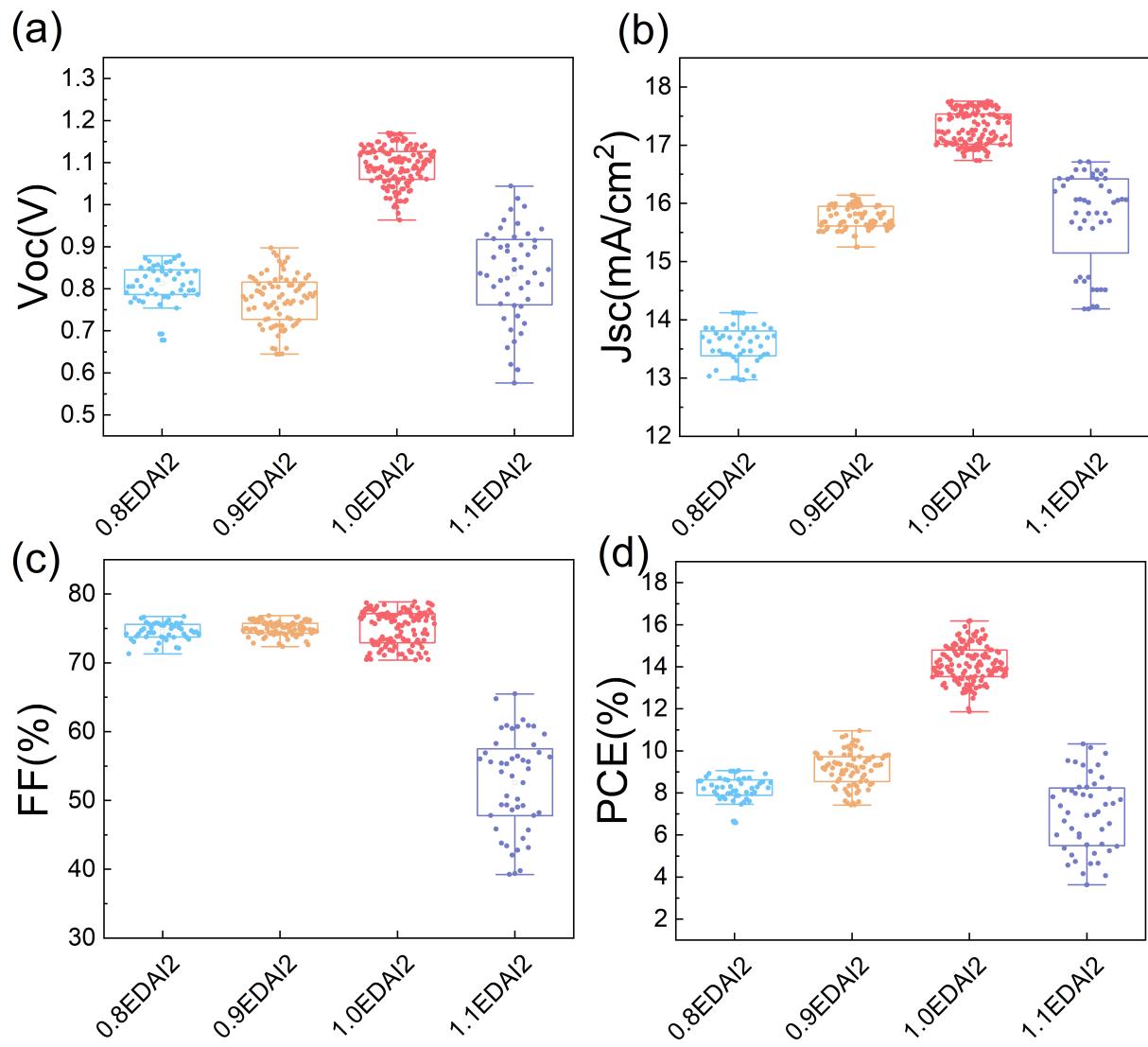


Fig. S11. Photovoltaic performance parameters: (a) V_{OC} , (b) J_{SC} , (c) FF, (d) PCE distribution of CsPbI₃ devices based on different EDAI₂ ratios (Pb(OAc)_2 : CsI: EDAI₂=1.2:1:X, X=0.8, 0.9, 1.0, 1.1). A total of 320 devices were measured.

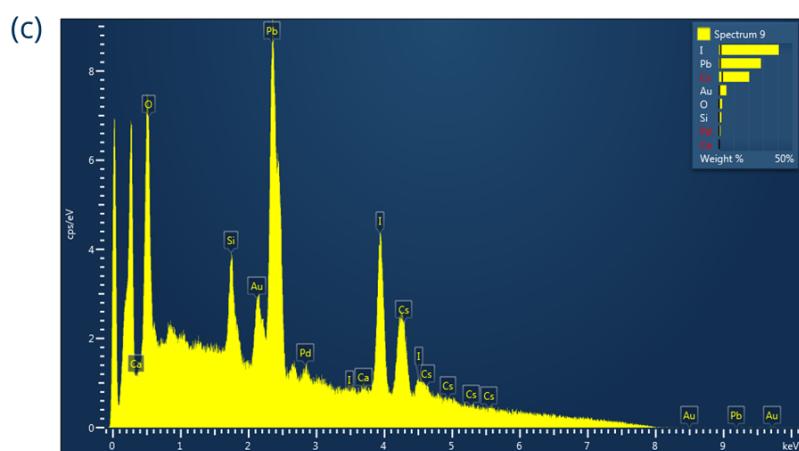
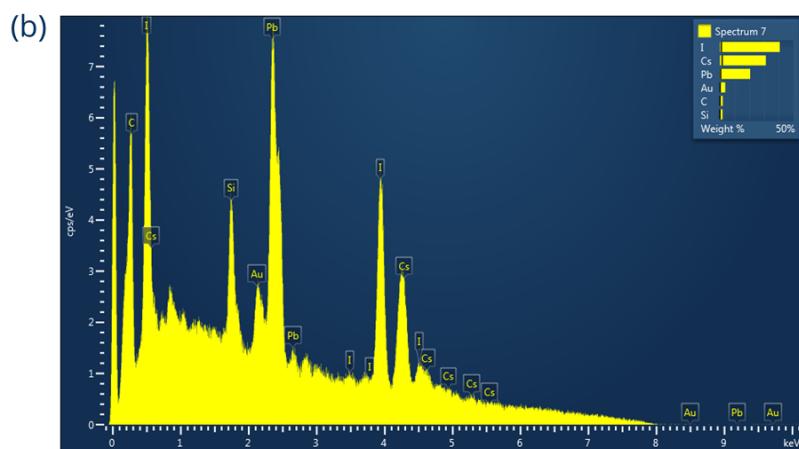
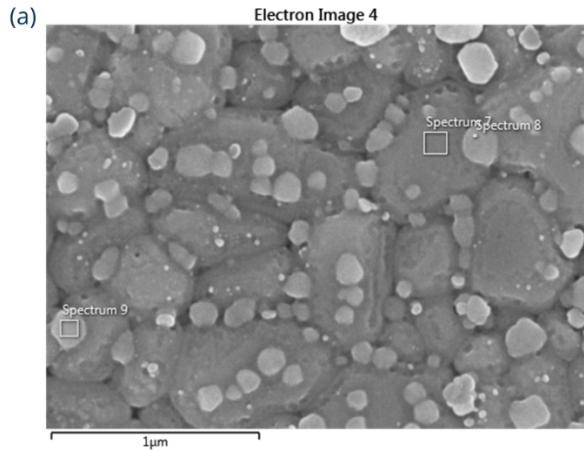


Fig S12. (a) Top-view SEM images and (b),(c) corresponding EDX element composition spectra in 1.2 samples on PTAA substrates.

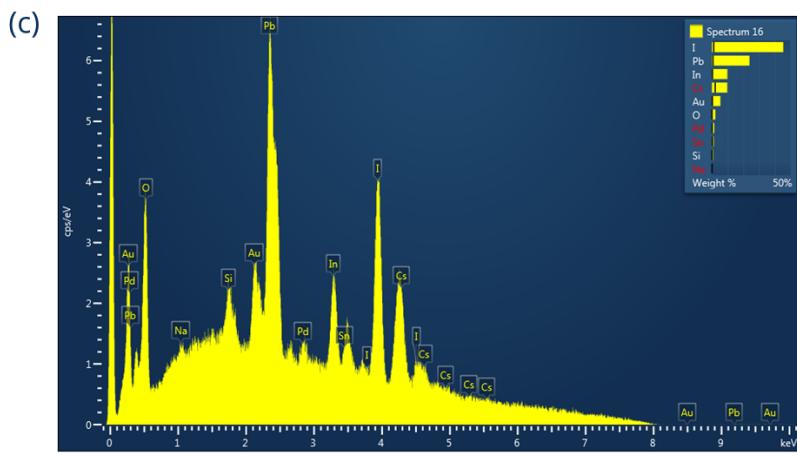
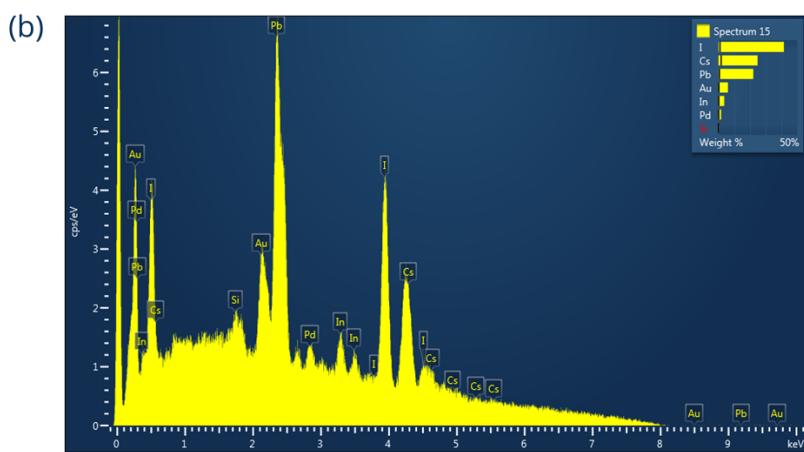
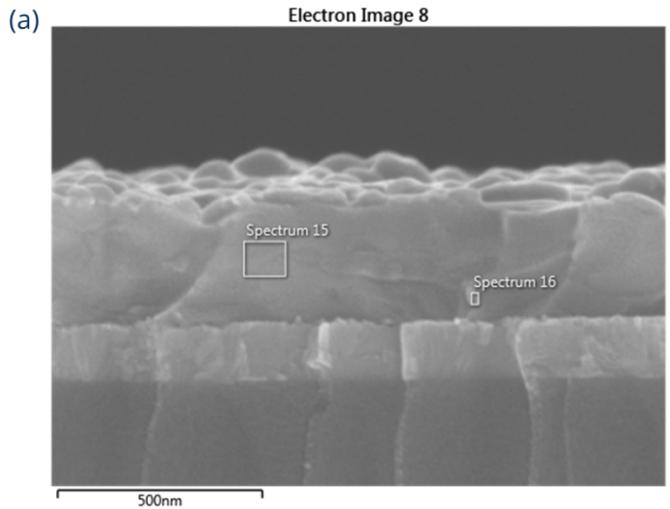


Fig S13.(a) Cross-sectional SEM images and (b)(c) corresponding EDX element composition spectra in 1.2 samples on PTAAs substrates.

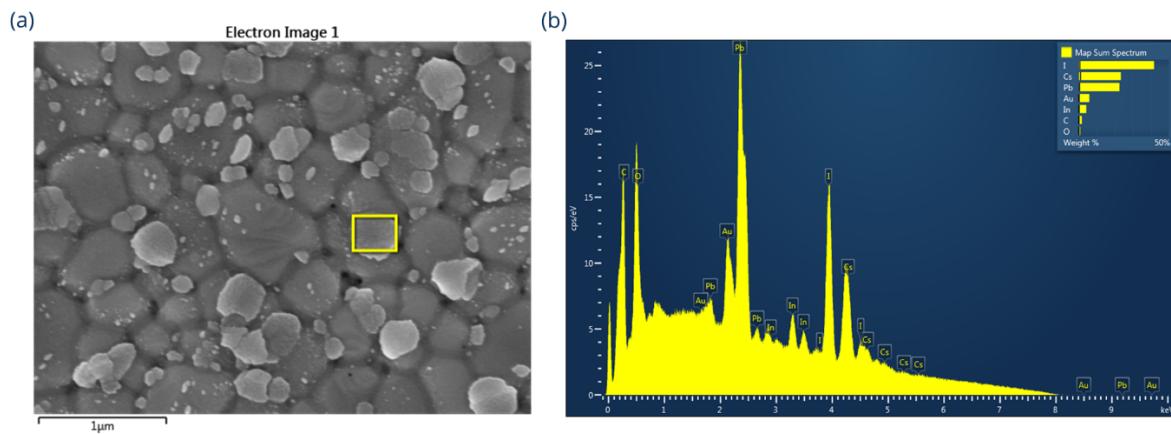


Fig S14. Top-view SEM images and corresponding EDX element composition spectra in 1.2 samples on MeO-2PACz substrates.

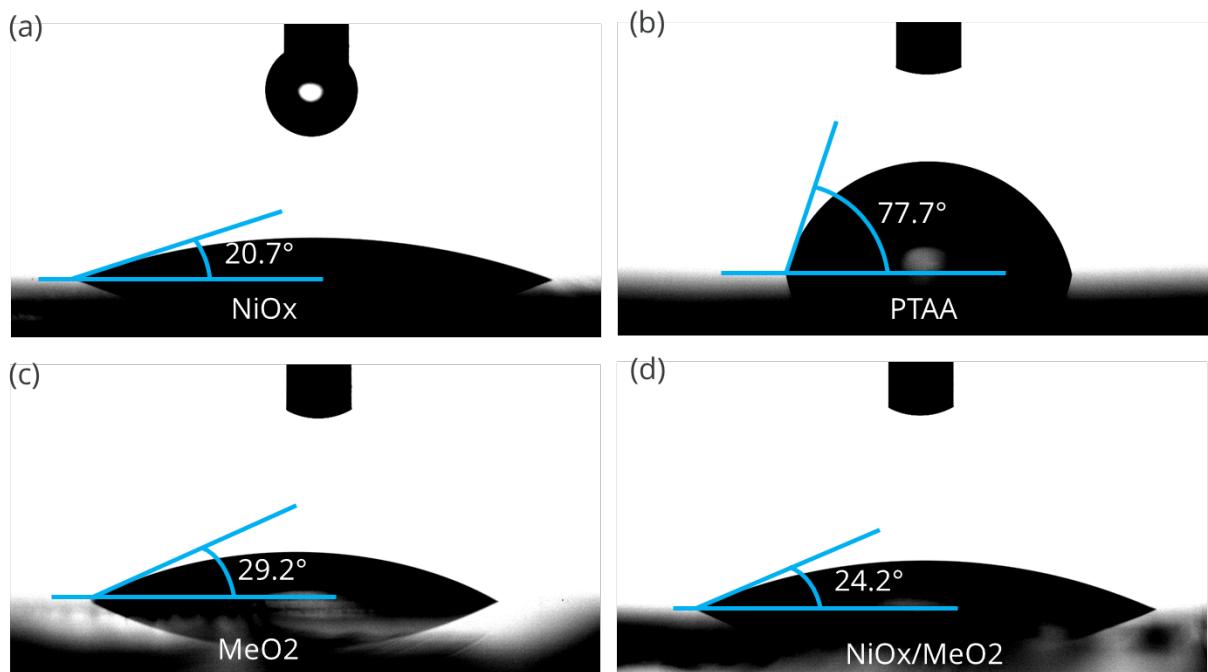


Fig. R15 Contact angle measurement of water on different HTLs: (a) NiOx, (b) PTAA, (c) MeO₂ and (d) NiOx/MeO₂ mixed hole transport layer.

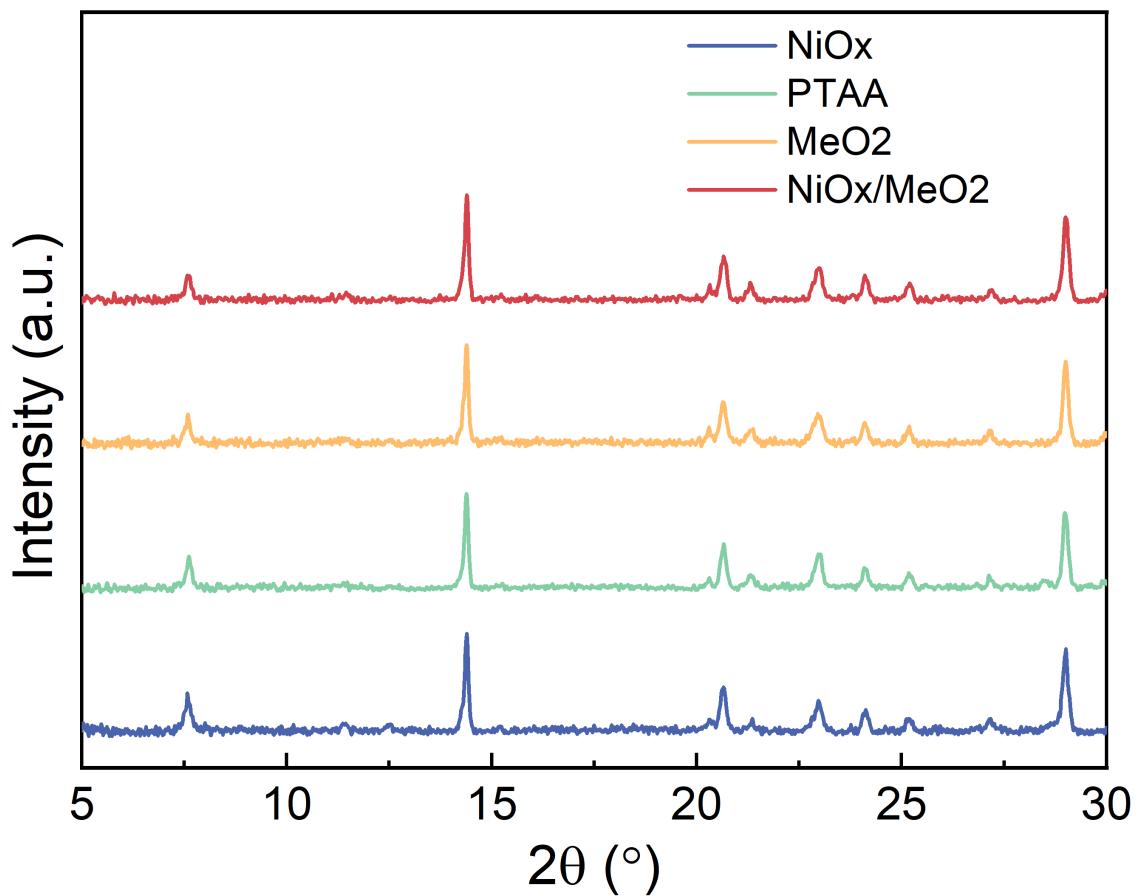


Fig. R16 XRD patterns of 1.2 CsPbI_3 on different hole transport layers.

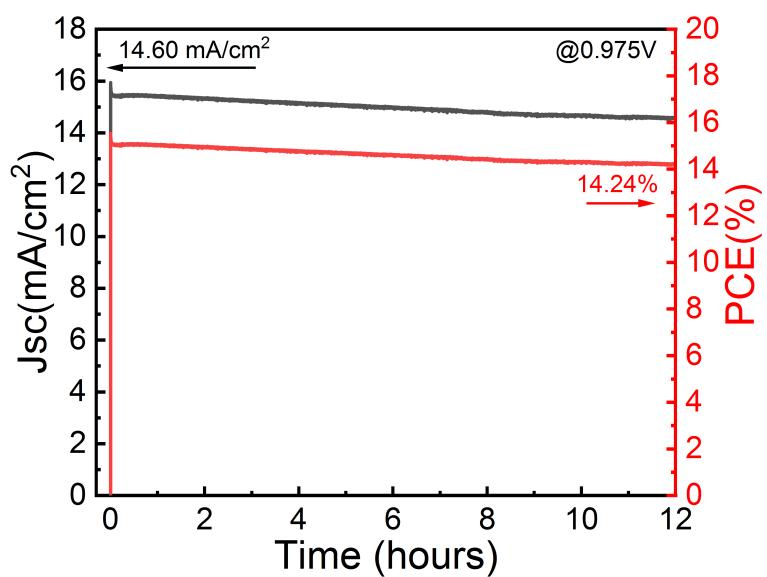


Fig S17. MPP tracking of 1.2 champion device on NiOx/MeO₂ HTL.

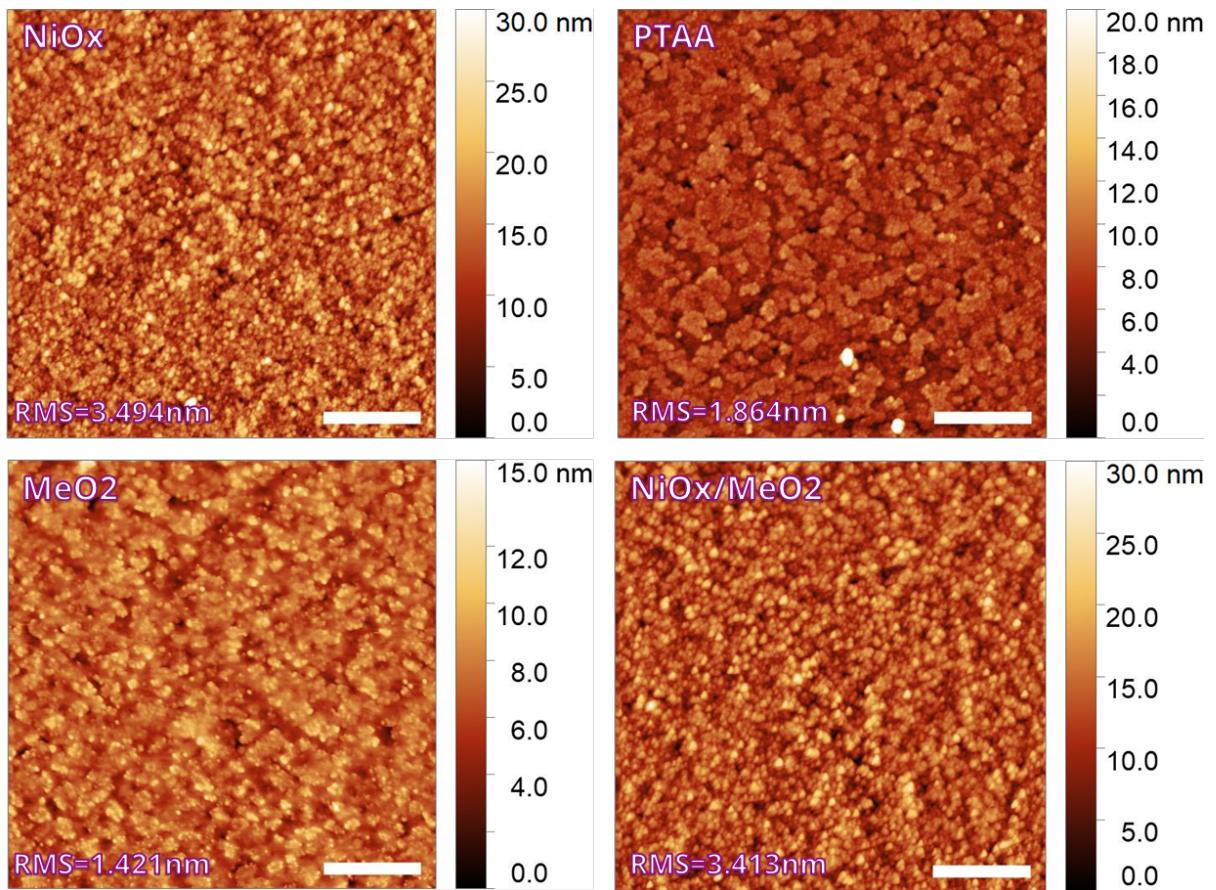


Fig S18. AFM images of different hole transport layer deposited on ITO substrates.

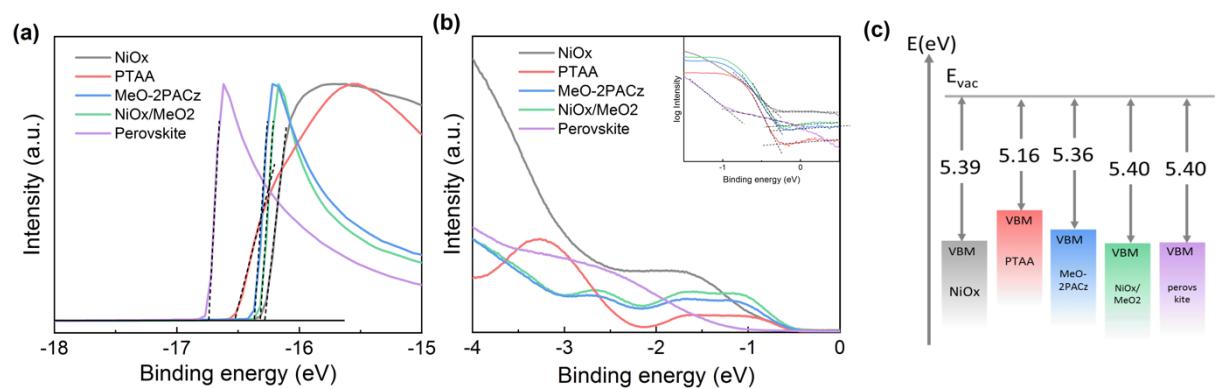


Fig S19. UPS spectra of 1.2 CsPbI₃ perovskite film, NiOx, PTAA, MeO-2PACz, NiOx/MeO2 deposited on ITO substrates. (a) SECO for determining the work function, (b) Binding energy range valence band spectra, (c) Energy level diagram for different HTLs and perovskite layer.

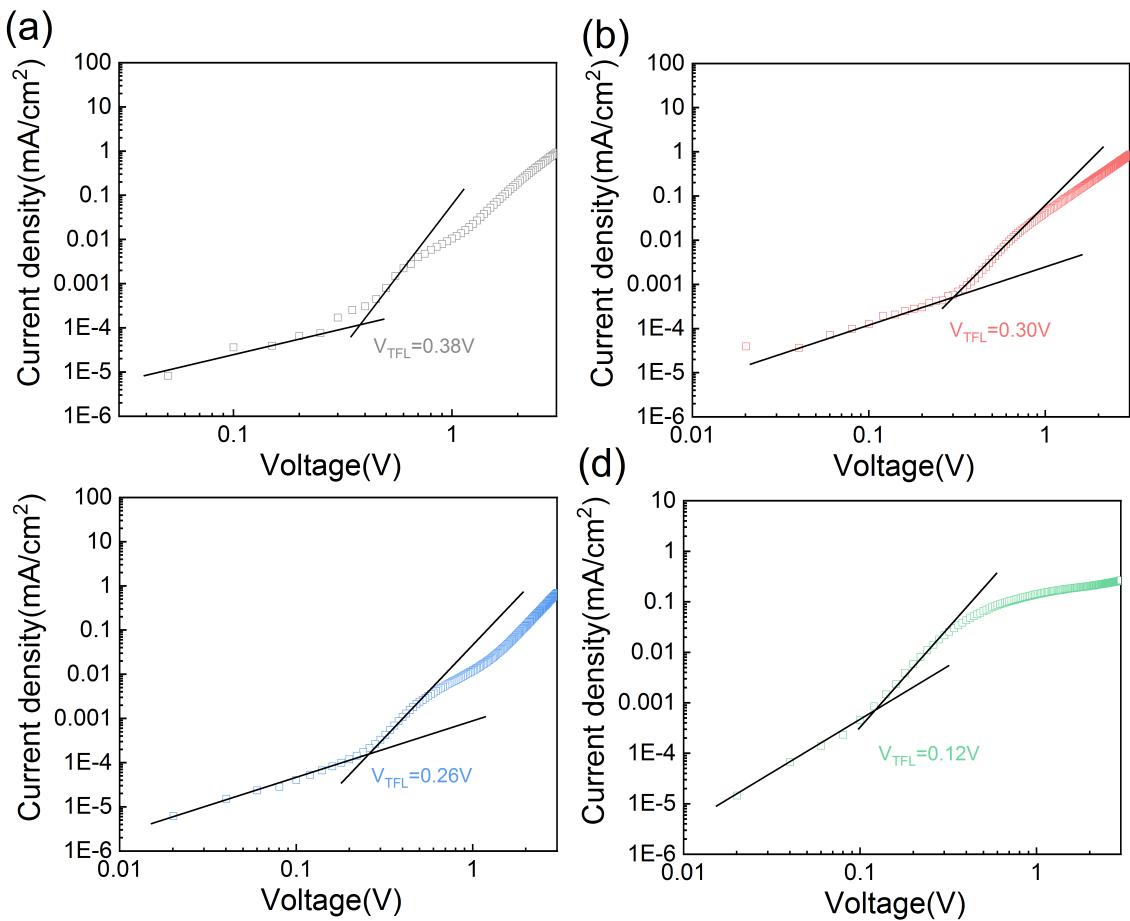


Fig S20. Dark I-V curves of perovskite devices on different hole transport layers: (a) NiOx, (b) PTAA, (c) MeO₂ and (d) NiOx/MeO₂. The device configuration is ITO/HTLs/perovskite/Spiro-OMeTAD/Au.

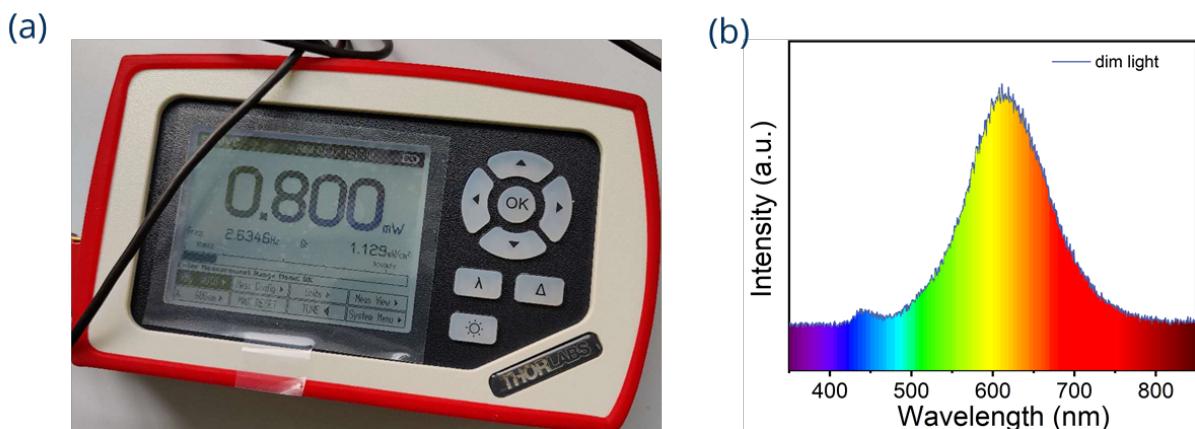


Fig. S21 Condition for shelf-storage measurement: (a) light intensity, (b) light spectrum.

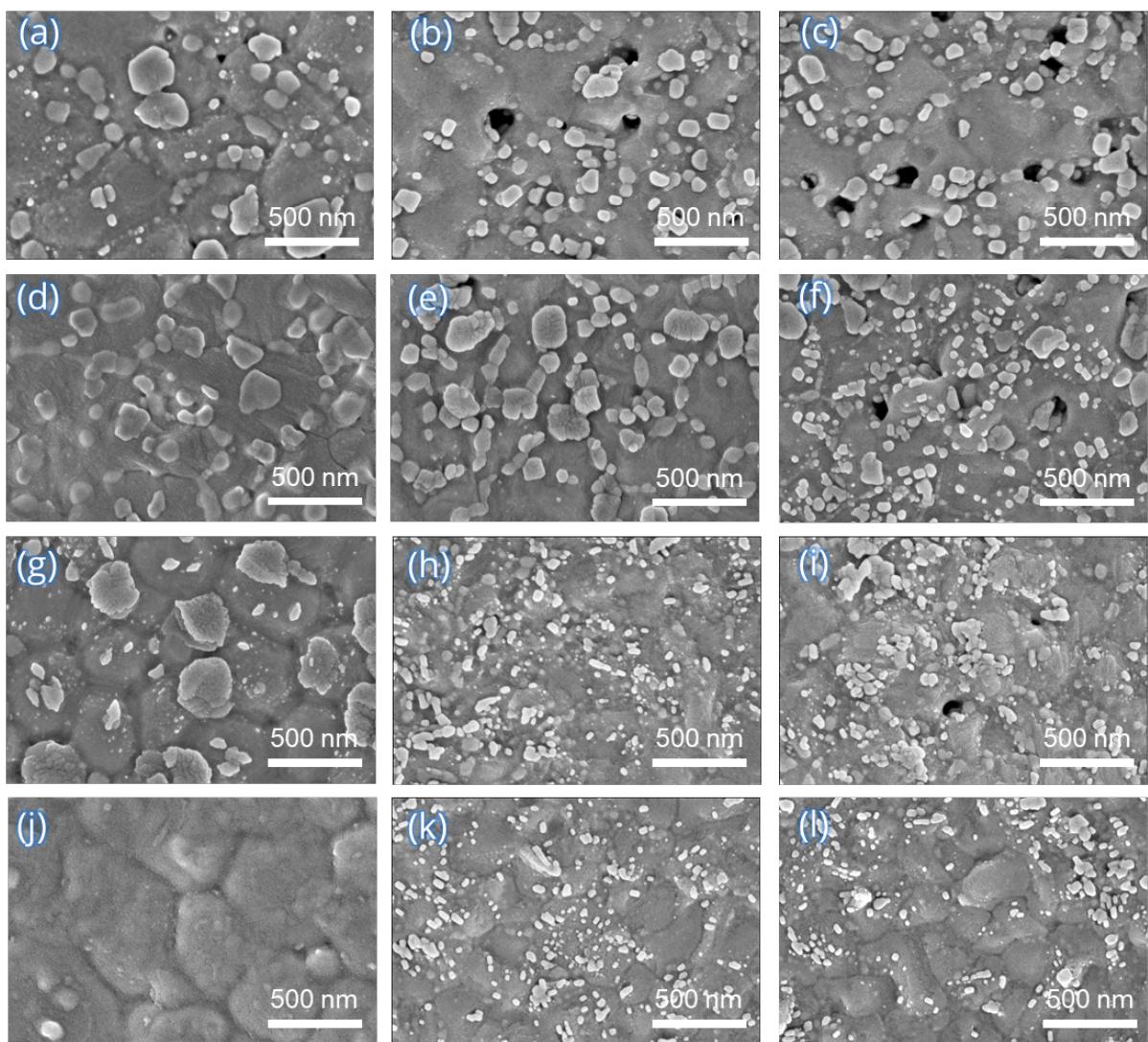


Fig. S22 SEM images of perovskite film on different HTLs under 1-sun illumination under nitrogen gas: NiOx with different time evolution (a) 0h, (b) 90h and (c) 200h; PTAA with different time evolution (d) 0h, (e) 90h and (f) 200h; MeO2 with different time evolution (g) 0h, (h) 90h and (i) 200h; NiOx/MeO2 with different time evolution (j) 0h, (k) 90h and (l) 200h.

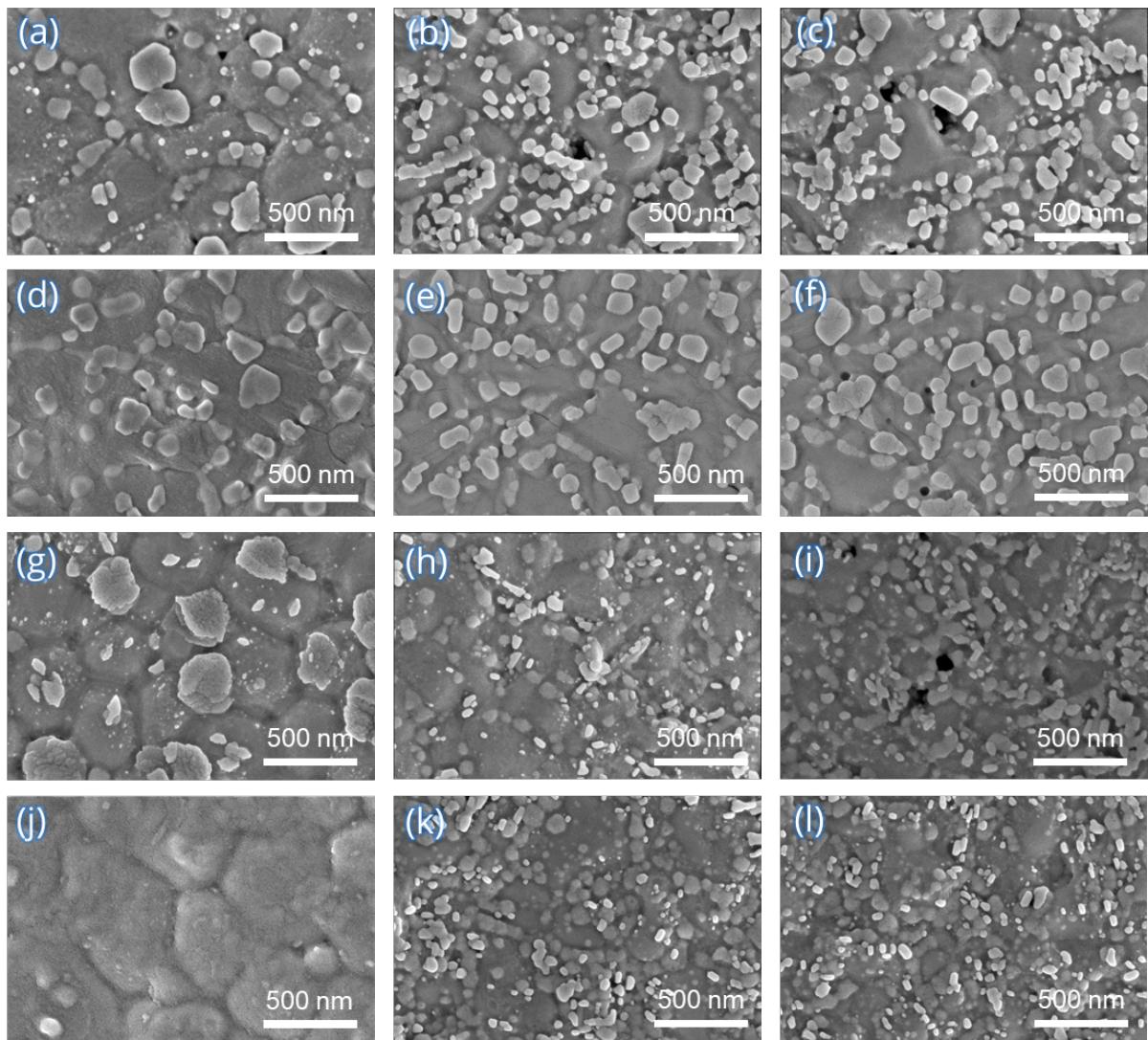


Fig. S23 SEM images of perovskite film on different HTLs under 1-sun illumination under nitrogen gas: NiOx with different time evolution (a) 0h, (b) 90h and (c) 200h; PTAA with different time evolution (d) 0h, (e) 90h and (f) 200h; MeO2 with different time evolution (g) 0h, (h) 90h and (i) 200h; NiOx/MeO2 with different time evolution (j) 0h, (k) 90h and (l) 200h.

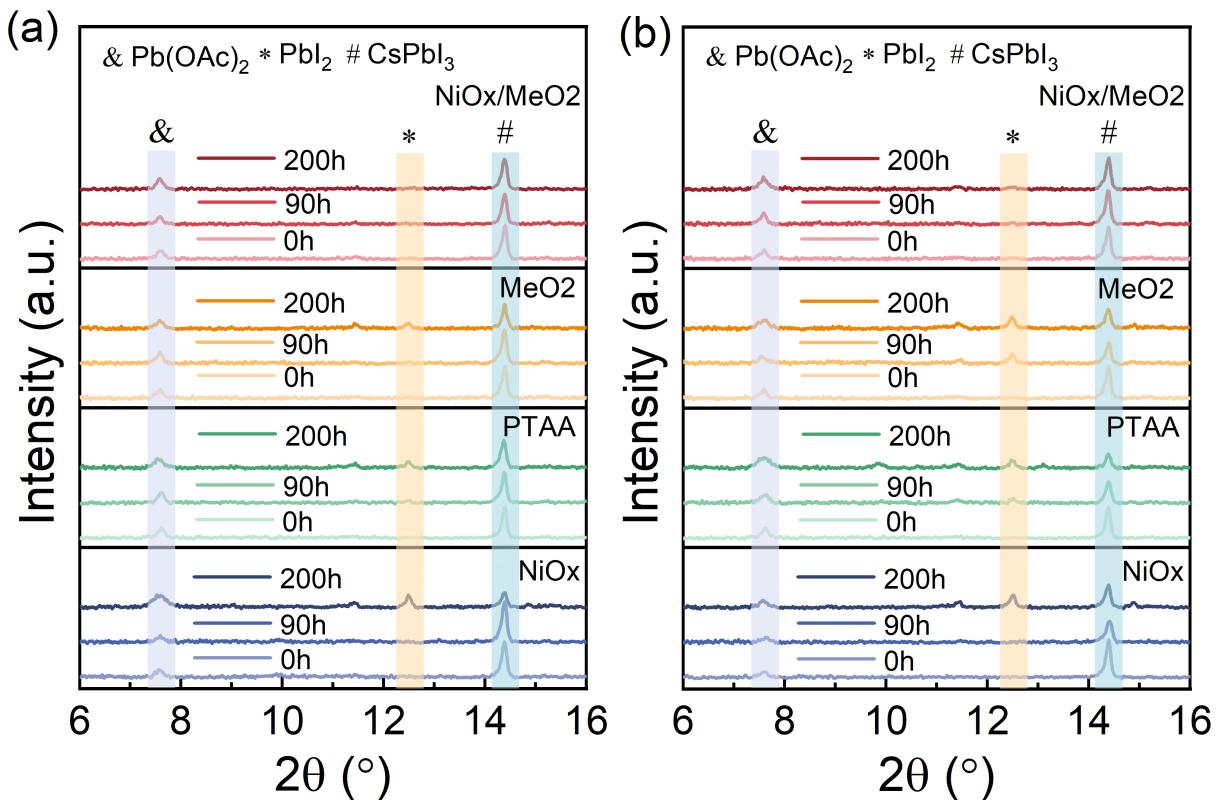


Fig. S24 XRD patterns of perovskite films on different substrates with time evolution under 1-sun illumination (a) and 80 °C heating (b).

Table S1 Element composition in 1.2Pb CsPbI₃ films varies with etching time

Etch Time (s)	Pb4f7 (%)	C1s (%)	O1s (%)	I3d5 (%)	Cs3d5 (%)
0	18.30	14.74	19.13	35.45	12.36
150	20.45	5.22	11.03	46.38	16.92
300	21.02	3.32	9.85	47.99	17.82
450	20.80	3.72	9.39	48.10	17.99
600	20.86	3.64	8.72	48.46	18.31

Table S2 Fitted carrier lifetime for different Pb(OAc)₂ excess

different Pb	A ₁	τ_1 /ns	A ₂	τ_2 /ns	A ₃	τ_3 /ns	τ_{ave} /ns
1.1	31286.82	0.84	8645.94	3.89	2837.27	10.54	5.21
1.15	12863.56	1.29	8321.98	4.92	2305.71	13.54	7.28
1.2	4603.23	2.08	8313.96	7.46	2224.01	18.26	10.91
1.25	14550.65	1.42	7725.36	5.01	1835.07	14.35	7.01
1.3	14393.03	1.15	8304.58	4.76	2510.24	12.32	6.76

Table S3 Photovoltaic performance parameters of champion cells with different Pb(OAc)₂ ratios (1.1, 1.15, 1.2, 1.25, 1.3)

Different Pb ratio	Voc [V]	Jsc [mA/cm ²]	FF [%]	PCE [%]
1.1-Forward	0.88	16.25	38.24	5.45
1.1-Reverse	0.84	16.25	55.32	7.57
1.15-Forward	1.07	16.83	66.15	11.93
1.15-Reverse	1.10	16.83	73.23	13.53
1.2-Forward	1.18	17.15	71.50	14.50
1.2-Reverse	1.20	17.15	76.60	15.81
1.25-Forward	1.00	16.64	68.71	11.42
1.25-Reverse	1.04	16.64	73.61	12.77
1.3-Forward	0.93	17.44	62.9	10.22
1.3-Reverse	0.97	17.44	66.04	11.12

Table S4 UPS spectra of different HTLs and 1.2Pb CsPbI₃ film

	WF (eV)	HOMO (eV)	IP (eV)
NiOx	4.93	0.46	5.39
PTAA	4.69	0.47	5.16
MeO2	4.85	0.51	5.36
NiOx/MeO2	4.90	0.50	5.40
Perovskite	4.46	0.94	5.40